1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in an enhanced LFPAK56E package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

2. Features and benefits

- Fully automotive qualified to AEC-Q101:
 - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
 - Reduced cell pitch enables enhanced power density and efficiency with lower R_{DSon} in same footprint
 - Improved SOA and avalanche capability compared to standard TrenchMOS
 - Tight V_{GS(th)} limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
 - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
 - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
 - · Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
 - Improved reliability, with reduced R_{th} and R_{DSon}
 - Increases maximum current capability and improved current spreading

3. Applications

- 12 V automotive systems
- · Motors, lamps and solenoid control
- · Start-Stop micro-hybrid applications
- · Transmission control
- · Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	220	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	500	W



N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK56E

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		0.6	0.85	1	mΩ
Dynamic chara	Dynamic characteristics						
Q_{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V; Fig. 13; Fig. 14		-	17.7	35.5	nC
Source-drain o	liode						
Q _r	recovered charge	I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V		-	53.2	-	nC
S	softness factor	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$		-	0.77	-	

^{[1] 220}A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		D
2	S	source		
3	S	source		G—CFA
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56E; Power- SO8 (SOT1023)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK7J1R0-40H	LFPAK56E; Power-SO8	plastic, single-ended surface-mounted package (LFPAK56); 4 leads; 1.27 mm pitch	SOT1023			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7J1R0-40H	71H040E

N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK56E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V_{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	500	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	220	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	[1]	-	220	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	600	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	diode			•		
I _S	source current	T _{mb} = 25 °C	[2]	-	165	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	600	Α
Avalanche ru	ggedness					-
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 190 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3] [4]	-	242	mJ

^{[1] 220}A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

^{[2] 165}A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

^[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

^[4] Refer to application note AN10273 for further information.

N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK56E

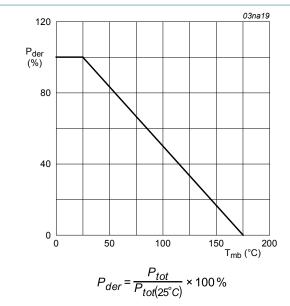
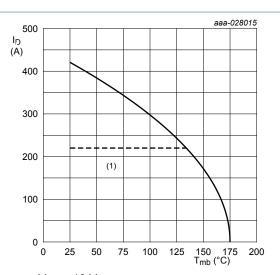


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



V_{GS} ≥ 10 V (1) 220A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature

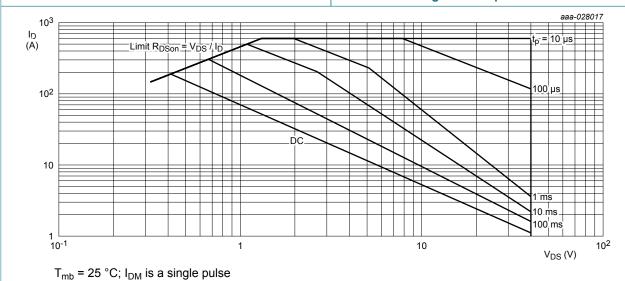
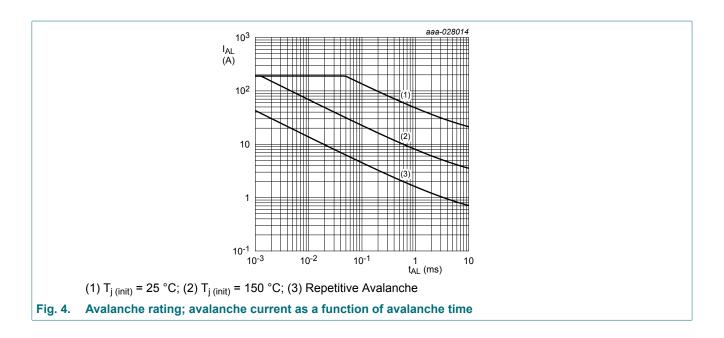


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

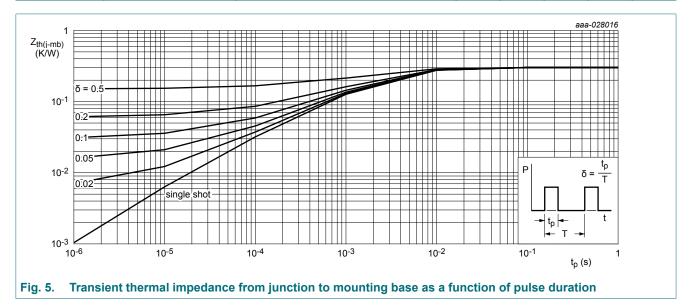
N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK56E



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.21	0.3	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	43	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -40 °C	-	40.5	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	36	40	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; <u>Fig. 9</u> ; <u>Fig. 10</u>	2.4	3	3.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 9$	-	-	4.3	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u>	1	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.07	1.5	μA
		V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C	-	3.2	25	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	0.34	1	mA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	0.6	0.85	1	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 105 °C; Fig. 12	0.84	1.27	1.6	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 125 °C; Fig. 12	0.93	1.41	1.75	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12	1.17	1.76	2.18	mΩ
R_G	gate resistance	f = 1 MHz; T _j = 25 °C	0.47	1.17	2.9	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V;	-	90.7	131	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	25.8	40	nC
Q_{GD}	gate-drain charge		-	17.7	35.5	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	6666	9340	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	1644	2300	pF
C _{rss}	reverse transfer capacitance		-	309	679	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω ; V_{GS} = 10 V;	-	22.2	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	18.9	-	ns
t _{d(off)}	turn-off delay time		-	51.7	-	ns
t _f	fall time		-	23.8	-	ns
Source-drai	in diode		1			-
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _i = 25 °C; <u>Fig. 16</u>	_	0.77	1.2	V

N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK56E

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/µs}; V_{GS} = 0 \text{ V};$	-	44.9	-	ns
Q _r	recovered charge	V _{DS} = 20 V	-	53.2	-	nC
S	softness factor	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$	-	0.77	-	
		I_S = 25 A; dI_S/dt = -500 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C; Fig. 17	-	0.68	-	

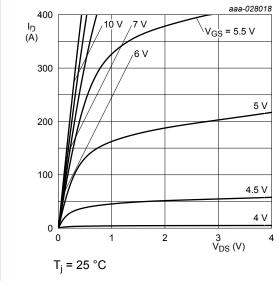


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

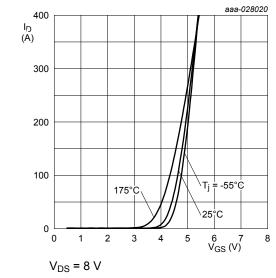


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

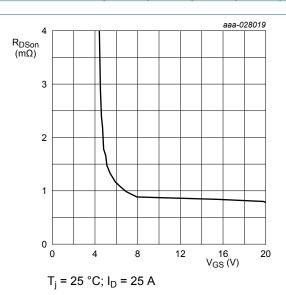


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

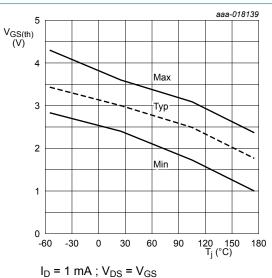


Fig. 9. Gate-source threshold voltage as a function of junction temperature

N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK56E

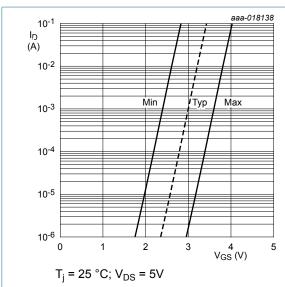


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

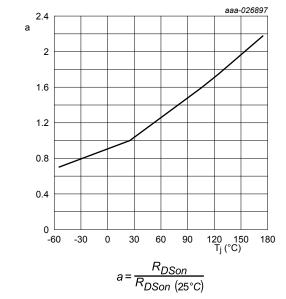


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

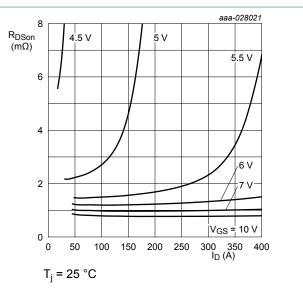


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

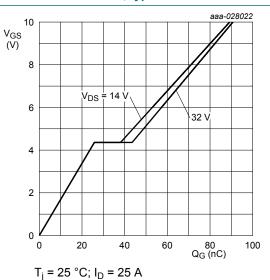


Fig. 13. Gate-source voltage as a function of gate charge; typical values

N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK56E

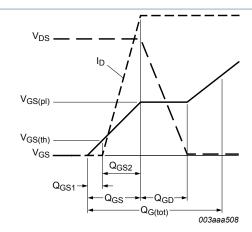
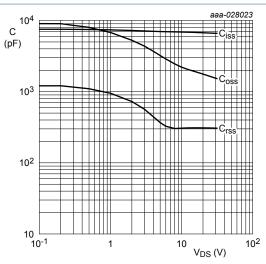


Fig. 14. Gate charge waveform definitions



 $V_{GS} = 0 V$; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

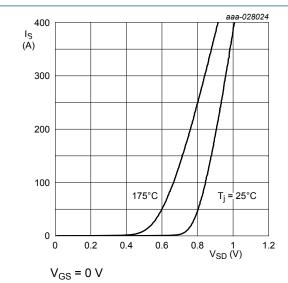
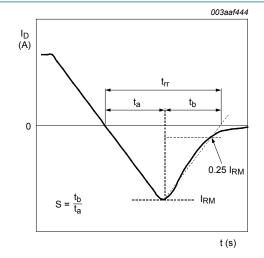


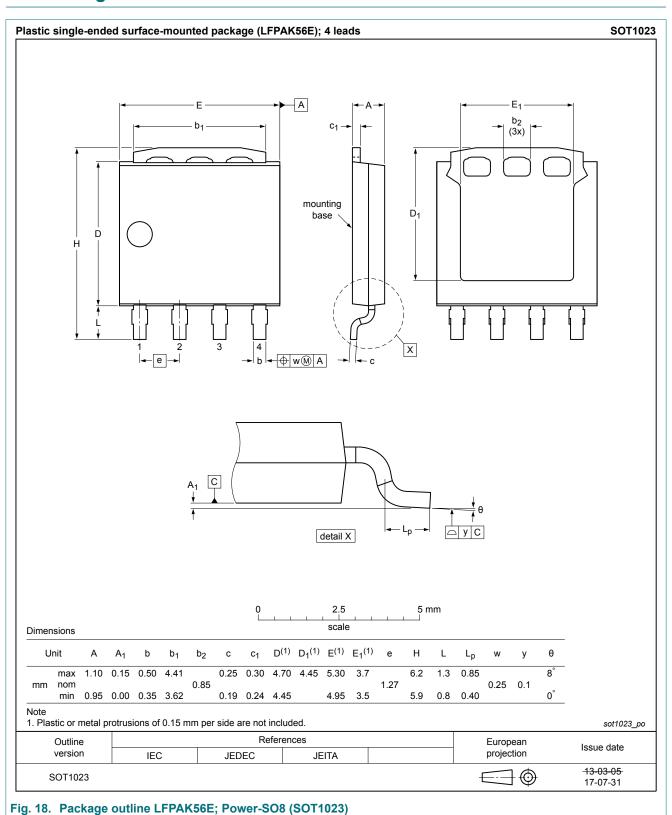
Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values



 $t_{rr} = t_a + t_b$

Fig. 17. Reverse recovery waveform definitions

11. Package outline



BUK7J1R0-40H

N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK56E

12. Legal information

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Document status [1][2]	Product status [3]	Definition
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BUK7J1R0-40H

N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK56E

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